



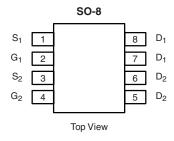
# **Dual N-Channel 30-V (D-S) MOSFET**

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)			
30	0.036 at V <sub>GS</sub> = 10 V	5.9			
30	0.053 at V <sub>GS</sub> = 4.5 V	4.9			

### **FEATURES**

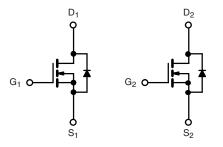
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si4936ADY-T1-E3 (Lead (Pb)-free)

Si4936ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	$T_A = 25$ °C, unles	ss otherwise r	noted		_	
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30			
Gate-Source Voltage		$V_{GS}$	± 20		V	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	5.9	4.4	^	
	T <sub>A</sub> = 70 °C		4.7	3.6		
Pulsed Drain Current		I <sub>DM</sub>	± 30		Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.7	0.9		
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.0 1.1		W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	L D	1.3	0.7	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical Maximum		Unit	
Manipular Landian La Angliànda	t ≤ 10 s	R <sub>thJA</sub>	50	62.5		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' 'thJA	90	110	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	32	40		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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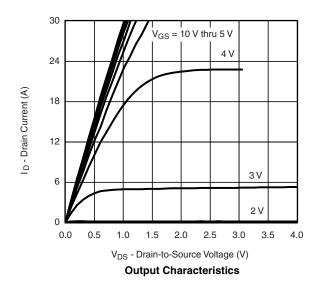
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1.0		3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	l	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1 ,,,		
	I <sub>DSS</sub>	$V_{DS}$ = 30 V, $V_{GS}$ = 0 V, $T_J$ = 55 °C			5	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Durin Course On Olate Besidence	B	$V_{GS} = 10 \text{ V}, I_D = 5.9 \text{ A}$		0.032	0.036		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 4.9 \text{ A}$		0.042	0.053	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.9 A		15		S	
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			13	20		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5.9 \text{ A}$		2.3		nC	
Gate-Drain Charge	$Q_{gd}$			2.0			
Turn-On Delay Time	t <sub>d(on)</sub>			6	12		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		14	25		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 10 V, $R_G$ = 6 $\Omega$		30	60	ns	
Fall Time	t <sub>f</sub>			5	10		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.7 A, dI/dt = 100 A/μs		30	60		

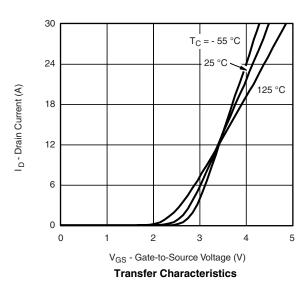
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



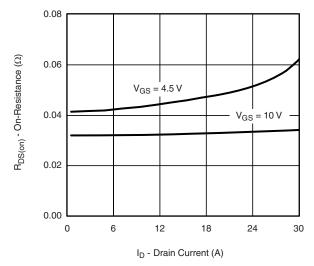




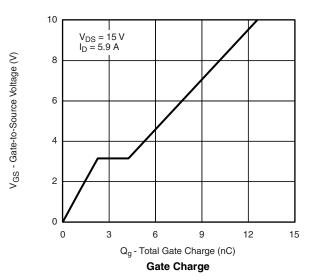


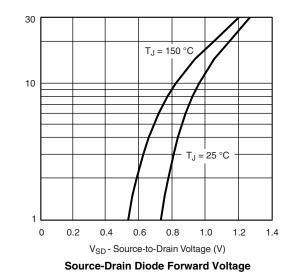


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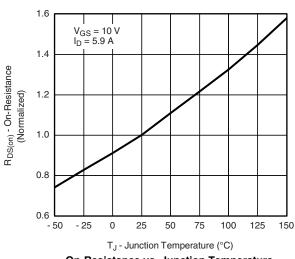
#### On-Resistance vs. Drain Current



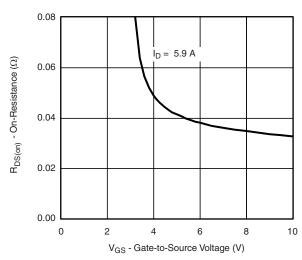


1000 800  $C_{\text{iss}}$ C - Capacitance (pF) 600 400 Coss 200 Crss 0 0 12 18 24 30

V<sub>DS</sub> - Drain-to-Source Voltage (V) Capacitance



On-Resistance vs. Junction Temperature



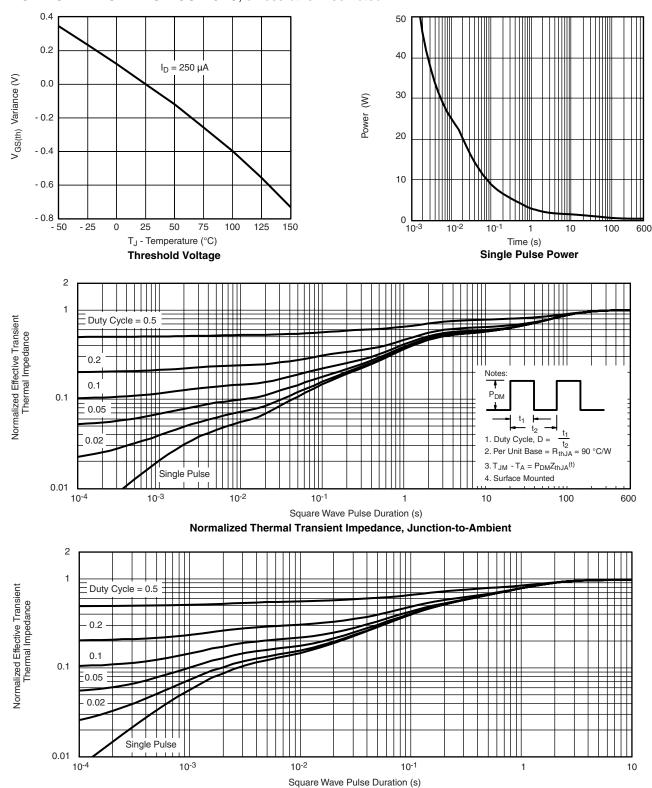
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?71132">www.vishay.com/ppg?71132</a>.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INC	HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
FCN: C-06527-Bey   11-Sen-06						

DWG: 5498

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## **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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